3DD510,3DD511,DD04,DD05

NPN Silicon Low Frequency High Power Transistor

Features:

1. Heavy output current.Small saturation voltage drop.Good output character.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, power amplify, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications			
			3DD510	3DD511	DD04	DD05
Collector-Emitter Voltage	V_{CEO}	V	300	250	160	60
Emitter-Base Voltage	V_{EBO}	V	5	5	5	5
Max. Collector Current	I_{CM}	A	15	10	3	6
Max. Collector Dissipation (Tc=75°C)	P_{CM}	W	100	100	30	30
Junction Temperature	T_{jm}	°C	175	175	175	175
Storage Temperature	T_{stg}	°C	-55~+175	-55~+175	-55~+175	-55~+175
Emitter-Base Laekage Current	I_{EBO}	mA				
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:2.0	Max.:2.0	Max.:1.0	Max.:1.0
			V_{CE}=150V	V_{CE}=125V	V_{CE}=150V	V_{CE}=50V
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:1.5	Max.:1.2	Max.:1.0	Max.:1.0
			I_C=3A,I_B=0.3A	I_C=5A,I_B=0.5A	I_C=1.5A,I_B=0.04A	I_C=6A,I_B=0.3A
DC Current Gain	h_{FE}		Min.:30	Max.:80 Min.:40	Max.:160 Min.:50	Max.:180 Min.:70
			V_{CE}= 5V, I_C=3A	V_{CE}= 5V, I_C=3.5A	V_{CE}= 5V, I_C=2A	V_{CE}= 5V, I_C=5A
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	300	250	160	60
			I_C=5mA	I_C=5mA	I_C=2mA	I_C=1mA
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5	5	5	5
			I_E=5mA	I_E=5mA	I_E=1mA	I_E=1mA

Outline and Dimensions: